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Karen (ing. mars 6/15/04

(Signature & date)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of :

June 15 2004

Bruce B. Doris, et al

Group Art No: 2818

Serial No. 10/604,190

Examiner: David Vu

Filed: 6/30/03

IBM Corporation Bldg. 300, Zip 482

Title: HIGH PERFORMANCE CMOS

2070 Route 52

DEVICE STRUCTURES AND METHOD

Hopewell Junction, NY 12533

OF MANUFACTURE

TITLE:

HIGH PERFORMANCE CMOS DEVICE STRUCTURES AND METHOD OF MANUFACTURE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or nonpertinency of the art, that better art than that listed is not available, or that other art is not applicable.

If any fees are required for this submission, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted, Bruce B. Doris, et al.

Joseph P. Abate

Registration No. 30,238

Telephone No. 845-894-4633

16-15-04

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